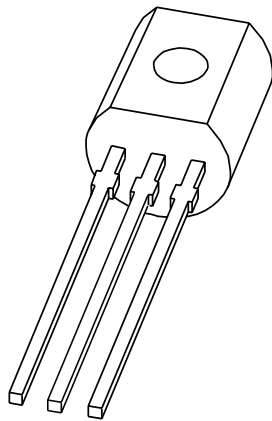


DATA SHEET



BS108

**N-channel enhancement mode
vertical D-MOS transistor**

Product specification
Supersedes data of 1997 Jun 17

2001 May 18

N-channel enhancement mode vertical D-MOS transistor

BS108

FEATURES

- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No secondary breakdown.

APPLICATIONS

- Line current interruptor in telephone sets
- Applications in relay, high-speed and line transformer drivers.

DESCRIPTION

N-channel enhancement mode vertical D-MOS transistor in a SOT54 (TO-92) package.

PINNING - SOT54

PIN	DESCRIPTION
1	source
2	gate
3	drain

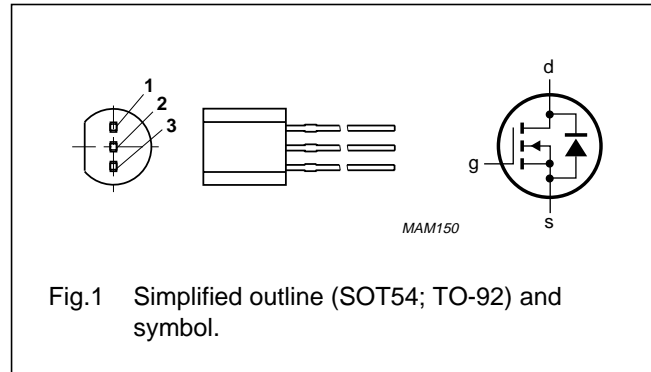


Fig.1 Simplified outline (SOT54; TO-92) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DS}	drain-source voltage (DC)	200	V
V_{GSth}	gate-source threshold voltage	1.8	V
I_D	drain current (DC)	300	mA
R_{DSon}	drain-source on-state resistance	5	Ω

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage (DC)		–	200	V
V_{GSO}	gate-source voltage (DC)	open drain	–	± 20	V
I_D	drain current (DC)		–	300	mA
I_{DM}	peak drain current		–	1.2	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$; note 1	–	1	W
T_{stg}	storage temperature		–55	+150	$^\circ\text{C}$
T_j	junction temperature		–	150	$^\circ\text{C}$

Note

1. Device mounted on a printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead minimum 10 × 10 mm.

N-channel enhancement mode vertical D-MOS transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	125	K/W

Note

1. Device mounted on a printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead minimum 10×10 mm.

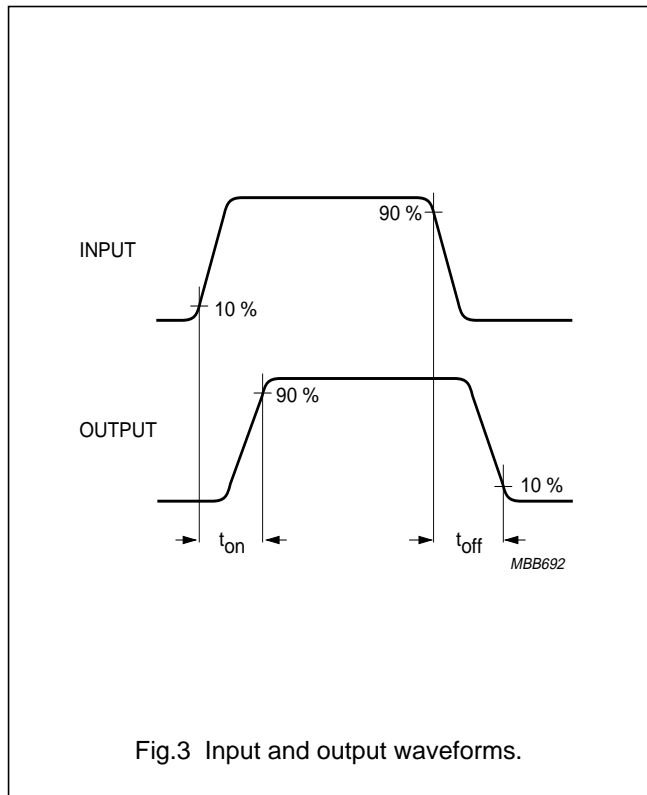
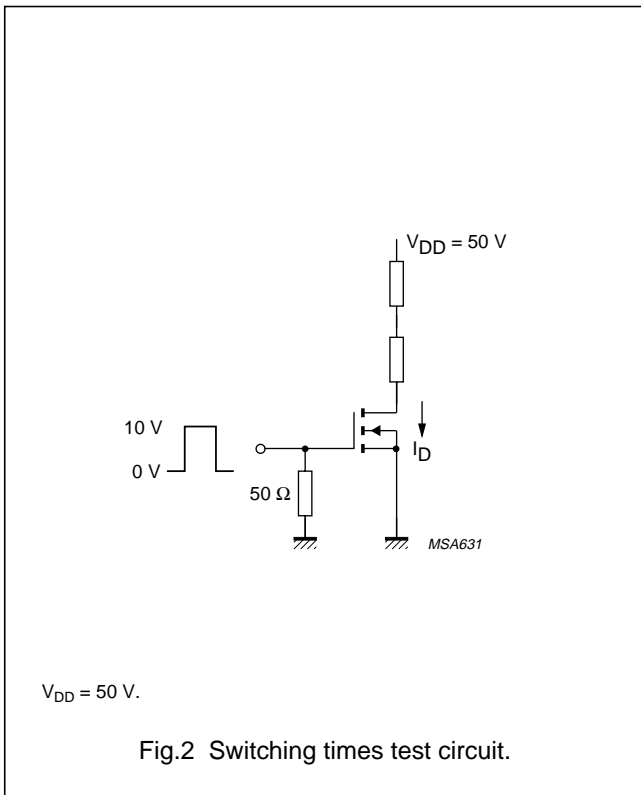
CHARACTERISTICS

$T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 10\ \mu A$; $V_{GS} = 0$	200	–	–	V
I_{DSS}	drain-source leakage current	$V_{DS} = 160$ V; $V_{GS} = 0$	–	–	1	μA
I_{GSS}	gate-source leakage current	$V_{GS} = \pm 20$ V; $V_{DS} = 0$	–	–	± 100	nA
V_{GSth}	gate-source threshold voltage	$I_D = 1$ mA; $V_{GS} = V_{DS}$	0.4	–	1.8	V
R_{DSon}	drain-source on-state resistance	$I_D = 100$ mA; $V_{GS} = 2.8$ V	–	2.7	5	Ω
$ Y_{fs} $	transfer admittance	$I_D = 300$ mA; $V_{DS} = 25$ V	200	600	–	mS
C_{iss}	input capacitance	$V_{DS} = 25$ V; $V_{GS} = 0$; $f = 1$ MHz	–	100	120	pF
C_{oss}	output capacitance	$V_{DS} = 25$ V; $V_{GS} = 0$; $f = 1$ MHz	–	20	30	pF
C_{rss}	reverse transfer capacitance	$V_{DS} = 25$ V; $V_{GS} = 0$; $f = 1$ MHz	–	10	15	pF
Switching times (see Figs 2 and 3)						
t_{on}	turn-on time	$I_D = 250$ mA; $V_{DD} = 50$ V; $V_{GS} = 0$ to 10 V	–	6	10	ns
t_{off}	turn-off time	$I_D = 250$ mA; $V_{DD} = 50$ V; $V_{GS} = 0$ to 10 V	–	49	60	ns

N-channel enhancement mode vertical D-MOS transistor

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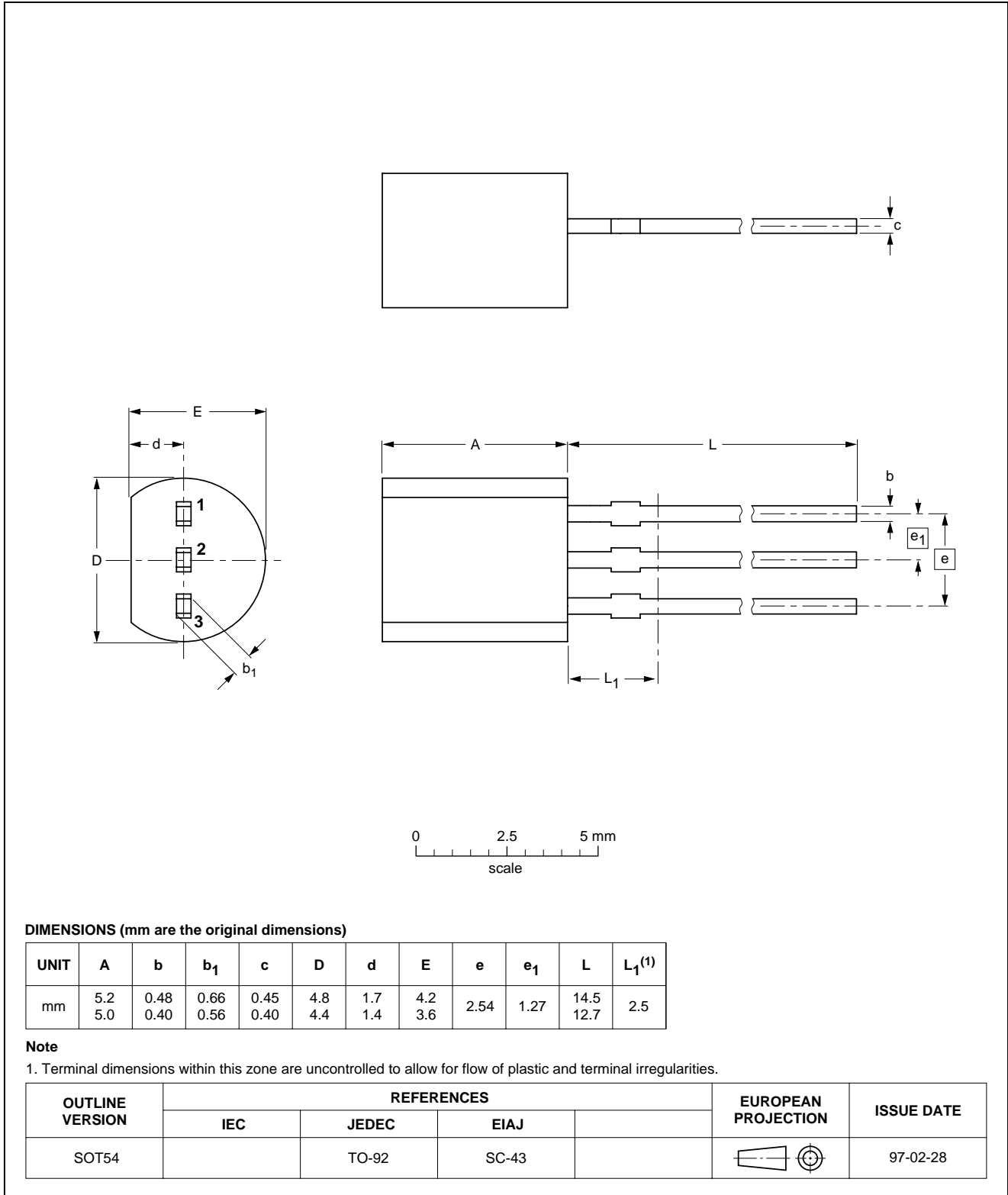
N-channel enhancement mode
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



N-channel enhancement mode vertical D-MOS transistor

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DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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vertical D-MOS transistor

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